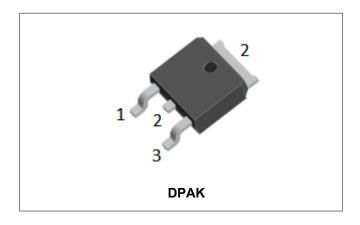


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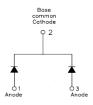
## MBRD10200CT SCHOTTKY RECTIFIER



## **Features**

- 150°C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: 100% Pure Tin
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## **Circuit Diagram**



#### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery charging

## **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	200	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @T <sub>C</sub> =105°C, rectangular wave form	5(Peg Leg) 10(Peg Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Peg Leg)	I <sub>FSM</sub>	8.3 ms, half Sine pulse	128	Α

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Peg Leg)*	V <sub>F1</sub> @ 5A, Pulse, T <sub>J</sub> = 25 °C		0.85	0.90	V
	V <sub>F2</sub>	@ 5A, Pulse, T <sub>J</sub> = 125 °C	0.70	0.74	V
Reverse Current (Peg Leg)*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 25 °C	0.0001	1	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 125 °C	0.05	25	mA
Junction Capacitance(Peg Leg)	Ст	$@V_R = 5V, T_C = 25  ^{\circ}C, f_{SIG} = 1MHz$	90	150	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

<sup>•</sup> China - Germany - Korea - Singapore - United States •

<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •



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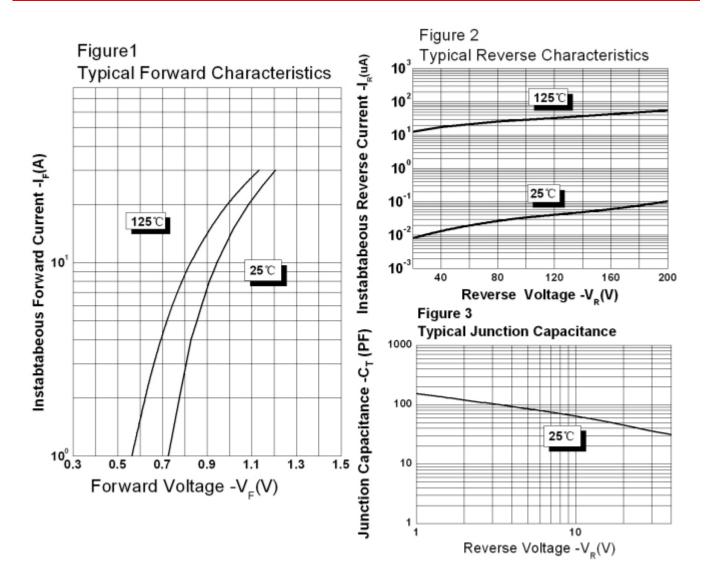




## **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to + 150	°C
Typical Thermal Resistance Junction to	В		3.5(per leg)	°C/W
Case	R <sub>θJC</sub>	-	2(per package)	-0/00
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			

## **Ratings and Characteristics Curves**



<sup>•</sup> China - Germany - Korea - Singapore - United States •

<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •

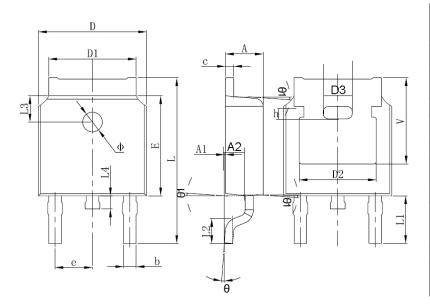


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## **Mechanical Dimensions DPAK**



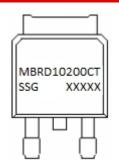
SYMBOL	Dimensions in millimeters			
	Min.	Тур.	Max.	
А	2.18	-	2.39	
A1	-	-	0.13	
b	0.64	-	0.89	
С	0.46	-	0.89	
D	6.35	-	6.73	
D2	4.32	-	-	
E	5.97	6.10	6.22	
е	2.29BSC			
L	9.40	-	10.41	
L2	1.40	1.52	1.78	
L4	-	-	1.02	
Θ	0°	-	10°	
V	5.21	-	-	

# **Ordering Information**

Device	Package	Shipping
MBRD10200CT	DPAK (Pb-Free)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel Packaging specification.

# **Marking Diagram**



Where XXXXX is YYWWL

MBR = Device Type
D = Package type
10 = Forward Current (10A)
200 = Reverse Voltage (200V)
CT = Configuration

 SSG
 = SSG

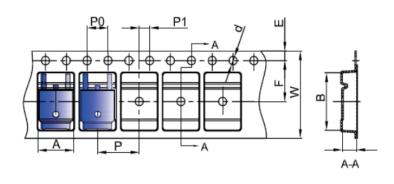
 YY
 = Year

 WW
 = Week

 L
 = Lot Number

**Cautions:** Molding resin Epoxy resin UL:94V-0

# Carrier Tape Specification DPAK



SYMBOL	Millimeters		
STWIBOL	Min.	Max.	
Α	6.80	7.00	
В	10.40	10.60	
С	2.60	2.80	
d	Ф1.45	Ф1.65	
E	1.65	1.85	
F	7.40	7.60	
P0	3.90	4.10	
Р	7.90	8.10	
P1	1.90	2.10	
W	15.90	16.30	

- China Germany Korea Singapore United States
  - http://www.smc-diodes.com sales@ smc-diodes.com •

#### MBRD10200CT



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